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Formation of CeSiO₄ from cerium(III) silicate precursors

Paul Estevenon⁵, Thibault Kaczmarek⁵, Fabien Vadot⁵, Thomas Dumas⁵, Pier Lorenzo Solarì⁵, Eleonore Welcombe⁵, Stephanie Szenknect⁵, Adel Mesbah⁵, Philippe Moisy⁵, Christophe Poinssot⁵, Nicolas Dacheux⁵

Even if the preparation of CeSiO₄ has already been reported, the formation of pure cerium silicate from aqueous precursors appears as a challenge. An innovative way of synthesis has been identified in this study allowing the formation of CeSiO₄ after hydrothermal treatment starting from Ce(III) silicate precursors. Among the experimental parameters examined, significant effects were found according to the nature of the precursor and reactive media considered, pH of the reactive media and temperature of the hydrothermal process. This study allows to determine optimized conditions for the hydrothermal synthesis of pure CeSiO₄ (A-Ce₂Si₅O₁₄ or Ce₁ Ce₂Si₆O₁₄) as starting precursors, nitric medium, pH = 7, 7 days at 150°C. In situ low oxidation rate of Ce(III) into Ce(V) was a key parameter to consider in order to avoid the presence of CeO₂ in the final mixtures.

Introduction

Cerium is often considered as a convenient surrogate in order to determine the behavior of plutonium in various systems, because Ce(III) and Ce(IV) chemistry are close to their plutonium counterparts and relatively representative of Pu(III)/Pu(IV) redox couple (E°(Ce(IV)/Ce(III)) = 1.72 V/ENH; ¹ E°(Pu(IV)/Pu(III)) = 1.047 ± 0.003 V/ENH⁻¹). In particular, Ce(III) silicate phases may be used to simulate isosctructural Pu(III) silicates, which have been reported in few studies only. CeSiO₄ is also isosctructural of ZrSiO₄, HfSiO₄ and AnSiO₄ (for An = Th, Pa, U, Np, Pu and Am) (space group I4/m amd). The formation of actinide silicate colloids was observed at room temperature for thorium, uranium(IV) and neptunium(IV) and was proved to modify the mobility of the actinides in the environment. The potential formation of Pu-based colloids in conditions representative of spent nuclear fuels repository settings deserves to be investigated. In this context, the study of cerium silicates appears as a compulsory first step to evaluate the behavior of plutonium in silicate-rich environments submitted to various redox conditions.

The preparation and characterization of Ce(III) silicates (Ce₂Si₅O₁₄, Ce₄(C₂O₄)₂O, A-Ce₂Si₅O₁₄ and G-Ce₂Si₅O₁₄) by high temperature routes has been extensively studied due to their potential applications. Indeed, these compounds have been identified as promising luminescent materials (in the blue/violet region) for scintillators and detectors applications. They have also been identified as very efficient ions exchangers for radionuclides separation and their formation has been reported as secondary phases for cerium doped zircon ceramics and cerium doped nuclear waste glasses. However, the behavior of Ce(III) silicate phases in wet reactive media has not been studied so far.

CeSiO₄ has been reported by Schlüter et al. as a natural occurring mineral phase formed in pegmatite rocks of the Stetind mount (Norway). The first synthesis of this silicate was reported by Dickson and Glasser in 2000. It consisted in the hydrothermal treatment of a mixture containing Ce(NO₃)₃·6 H₂O and CaO under inert atmosphere between 55 and 180°C. The formation of CeSiO₄ samples using a wet chemistry route from Ce(III) nitrate or chloride at temperatures ranging from 40°C to 150°C in weakly basic conditions has been reported recently. These results highlighted that the use of Ce(III) was required to prepare CeSiO₄. Indeed, all the attempts to form CeSiO₄ from Ce(IV) precursors failed due to the precipitation of cerium tetrahydroxide, leading to CeO₂ by ageing. Consequently, the use of reactive conditions that may disfavor cerium hydrolysis constitutes a key parameter to prepare pure CeSiO₄. The formation of CeSiO₄ from crystalline Ce(III) silicate phases through a dissolution and oxidation process could also be considered as an alternative way of synthesis. Moreover, due to cerium representativity as a plutonium surrogate, this study may provide crucial information on plutonium silicate chemistry and, therefore, on the behavior of plutonium in the environment. In this context, this paper reports a comprehensive study of the formation of CeSiO₄ by chemical degradation of solid Ce(III) silicate precursors.

Table 1. Conditions of formation of Ce(III) silicate precursors and associated lattice parameters determined by Rietveld refinement.

<table>
<thead>
<tr>
<th>Compound</th>
<th>Space group</th>
<th>Grinding step</th>
<th>Thermal treatment</th>
<th>Unit cell parameters</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ce₂Si₅O₁₄</td>
<td>P12₁/c1 (14)</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Ce₄(C₂O₄)₂O</td>
<td>P6₃/m (176)</td>
<td>1h – 30 Hz</td>
<td>9h – 1350°C Ar - 4% H₂</td>
<td>9.2775(3) 7.3942(3) 6.9665(3) 108.33(1)</td>
</tr>
<tr>
<td>A-Ce₂Si₅O₁₄</td>
<td>P4₁ 76</td>
<td></td>
<td></td>
<td>9.6505(4) 7.0738(3)</td>
</tr>
<tr>
<td>G-Ce₂Si₅O₁₄</td>
<td>P2₁/n (14)</td>
<td>1h – 30 Hz</td>
<td>9h – 1550°C Ar - 4% H₂</td>
<td>8.7245(4) 13.0735(6) 5.4031(3) 90.13(1)</td>
</tr>
</tbody>
</table>
Materials and methods

Syntheses

Reactants. All of the reagents used were of analytical grade and supplied by Sigma-Aldrich. Na₂SiO₃ was used as the silicate precursor. CeO₂ (99.9 %) and SiO₂ (99.5 %) were used as solid precursors to prepare high-temperature Ce(III) silicate phases. 0.75 mol·L⁻¹ HNO₃ and HCl solutions were prepared by dilution of Sigma Aldrich ACS grade concentrated HNO₃ (70%) and HCl (37%) solutions. 8 mol·L⁻¹ NaOH solution was also freshly prepared from Sigma Aldrich ACS grade NaOH (98 %) before the experiments.

Preparation of Ce(III) silicates precursors. Ce(III) silicate precursors were prepared considering the protocol described by Zec et al. for Ce₃SiO₈ (space group P12₁/c1), Ce₄Si₇(SiO₄)₃O (space group P6₃/m), tetragonal Ce₂Si₃O₇ (space group P4₃/m, named “A-Ce₃Si₃O₇”) and monoclinic Ce₂Si₃O₇ (space group P2₁/n, named “G-Ce₃Si₃O₇”). The samples were prepared by mixing CeO₂ and SiO₂ in stoichiometric conditions with respect to the targeted materials. Homogenization of the powders was performed by mechanical milling step (30 Hz, 1 hour) in a tungsten carbide milling vessel thanks to a Retsch MM 200 vibration mill mixer. The samples were then pelleted by isostatic pressing under 5 MPa at room-temperature and heated at high temperature under Ar – 4% H₂ atmosphere in order to favor the cerium reduction, as described in Table 1.

Preparation of CeSiO₄ from Ce(III) silicate precursors. Ce(III) silicate based precursors were placed in contact with 0.75 mol·L⁻¹ HNO₃ or HCl solution in air (no dissolution was evidenced in these conditions). The pH was then adjusted to the final value with 8 mol·L⁻¹ NaOH solution. The mixtures were put in Teflon lined reactors in Parr autoclaves and then treated in hydrothermal conditions for 1 to 20 days between 60°C to 250°C and under autogenous pressure (reaction conditions were fixed to 7 days and 150°C, respectively (Table S1). The obtained precipitates were then separated from the supernatant by centrifugation for 12 min at 14 000 rpm, washed twice with deionized water and once with ethanol, and finally dried overnight at 60°C in an oven. The samples were characterized by PXRD, infrared and Raman spectroscopies, SEM and XAS.

Characterization

The synthesized compounds were analyzed by PXRD with the help of a Bruker D8 advance diffractometer equipped with a lynxeye detector and using Cu Ka radiation (λ = 1.54184 Å) in a reflection geometry (parallel beam). PXRD patterns were recorded between 5° and 100° (2θ) with steps of 0.019° and a total counting time of 2.5 to 3 hours per sample. Pure silicon was used as a standard material to extract the instrumental parameters. All the collected data were refined by the Rietveld method using the Fullprof_Suite package. During the refinements, different profile and structure parameters were allowed to vary, such as the zero shift, unit-cell parameters, scale factor, and overall displacement factor. However, the occupancy of each site was fixed to the calculated values. Raman spectra were recorded with a Horiba-Jobin Yvon Aramis device equipped with an edge filter and a Nd:YAG laser (532 nm) that delivered 60 mW at the surface of the sample. In order to

Figure 1. PXRD diagrams of prepared Ce₃SiO₈, Ce₄Si₇(SiO₄)₃O, A-Ce₃Si₃O₇ and G-Ce₃Si₃O₇, calculated and difference profiles after Rietveld refinement. XRD lines of sample holder are pointed out by an asterisk.

The as-prepared samples were characterized by Powder X-Ray Diffraction (PXRD), infrared and Raman spectroscopies and Scanning Electron Microscopy (SEM). The presence of cerium oxides was never detected in the samples. Moreover, Rietveld refinement of the diagrams did not show significant differences of the lattice parameters compared to those reported in the literature (Table S1 and Figure S2).

Infrared and Raman spectra were also recorded for each compound before and after hydrothermal treatment (Figure S1 and Figure S2).

Preparation of CeSiO₄ from Ce(III) silicate precursors. Ce(III) silicate based precursors were placed in contact with 0.75 mol·L⁻¹ HNO₃ or HCl solution in air (no dissolution was evidenced in these conditions). The pH was then adjusted to the final value with 8 mol·L⁻¹ NaOH solution. The mixtures were put in Teflon lined reactors in Parr autoclaves and then treated in hydrothermal conditions for 1 to 20 days between 60°C to 250°C and under autogenous pressure (reaction conditions were fixed to 7 days and 150°C, respectively (Table S1). The obtained precipitates were then separated from the supernatant by centrifugation for 12 min at 14 000 rpm, washed twice with deionized water and once with ethanol, and finally dried overnight at 60°C in an oven. The samples were characterized by PXRD, infrared and Raman spectroscopies, SEM and XAS.

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avoid any laser-induced degradation of the compound, the power was turned down by the means of optical filters. The laser beam was then focused on the sample using an Olympus BX 41 microscope with a X50LMP objective, resulting in a spot area of ~1 μm² and a power of 475 μW for CeSiO₄ samples and of 3.8 mW for Ce(III) silicates. For each spectrum, a dwell time ranging from 30 to 600 s was used. All the recorded spectra corresponded to the average of four scans in order to minimize the measurement error. Moreover, the data were collected on different areas for each sample.

FTIR spectra were recorded in the 300–4000 cm⁻¹ range with a Perkin-Elmer FTIR Spectrum 100 device. Powdered samples were deposited on the surface of an ATR crystal without any prior preparation. The spectra collected in such operating conditions exhibited a resolution lower than 4 cm⁻¹. Four scans were performed to average the measurement error.

SEM observations were directly conducted on small powder samples without any prior preparation such as metallization, using a FEI Quanta 200 electronic microscope, equipped either with an Everhart-Thornley Detector (ETD) or a Back-Scattered Electron Detector (BSED), under high vacuum conditions with a very low accelerating voltage (2 – 3.1 kV). These conditions were chosen in order to create a beam deceleration effect that led to high resolution images.

The extended X-ray absorption fine structure (EXAFS) and X-Ray Absorption Near Edge Structure (XANES) spectroscopy measurements were carried out at the MARS Beamline at the SOLEIL synchrotron facility (Saint Aubin). The spectra were collected in the fluorescence mode at room temperature. Measurements were performed at the cerium L₃ edge (5723 eV). Data reduction and extraction of EXAFS oscillation was performed using the Athena and Artemis package. The threshold energy, E₀, was defined as the maximum of the first derivative of the absorption coefficient. Theoretical phase shifts and backscattering amplitudes were obtained with the ab initio code FEFF8.2 using the CeSiO₄ structures.

### Results and discussion

#### Preparation of CeSiO₄ in nitric media

All attempts to prepare CeSiO₄ were made from Ce₂SiO₅, Ce₄Sₓ(2-x)(SiO₂)ₓO, A-Ce₂SiO₅ and G-Ce₂SiO₅ precursors and Na₂SiO₃ as complementary silicon source in order to maintain the Ce:Si stoiχiometry of CeSiO₄.

These experiments were performed in nitric acid with 8.4 x 10⁻⁴ mol of cerium and silicon in 4 mL (leading to a concentration of 0.21 mol·L⁻¹ when considering the total dissolution of cerium and silicon), initial acid conditions ranging from C₃H₄N₃ = 1.3 mol·L⁻¹ to pH = 11.7, air atmosphere and with a hydrothermal treatment of 7 days at 150°C.

For each precursor, hydrothermal treatments allowed the formation of CeSiO₄ on a wide pH range:
- from C₃H₄N₃ = 0.7 mol·L⁻¹ to pH = 8.4 starting from Ce₄Sₓ(2-x)(SiO₂)ₓO (Figure 2);
- from C₃H₄N₃ = 1.3 mol·L⁻¹ to pH = 8.1 starting from A-Ce₂SiO₅ (Figure 3);
- from pH = 1.0 to pH = 8.5 starting from Ce₂SiO₅ (Figure S3);
- from pH = 1.0 to pH = 8.2 starting from G-Ce₂SiO₅ (Figure S4).

The syntheses performed in very acidic media (i.e. for C₃H₄N₃ > 0.3 mol·L⁻¹) usually led to the simultaneous precipitation of

![Figure 3. PXRD patterns obtained after hydrothermal treatment (7 days, T = 150°C) under air atmosphere starting from A-Ce₂SiO₅ precursor in nitric acid media and with an initial pH equal to 11.1 (8), 8.1 (9), 7.0 (10), 4.0 (11), 2.0 (12), C₃H₄N₃ = 0.7 mol·L⁻¹ (13) and C₃H₄N₃ = 1.3 mol·L⁻¹ (14). XRD lines of sample holder are pointed out by an asterisk. Characteristic XRD lines of CeO₂, Ce₅O₇ and A-Ce₂SiO₅ were extracted from ref 32, 9 and 24, respectively.](image)

![Figure 4. PXRD patterns obtained when using A-Ce₂SiO₅ as starting precursor, after hydrothermal treatment performed at 150°C under air atmosphere in nitric media and pH = 7 for 1 day (15), 3 days (16) and 7 days (10). XRD lines of sample holder are pointed out by an asterisk. Characteristic XRD lines of CeO₂, Ce₅O₇ and A-Ce₂SiO₅ were extracted from ref 32, 9 and 24, respectively.](image)
amorphous SiO$_2$ and solubilization of cerium as Ce$^{3+}$ in solution. Only small amounts of cerium were precipitated as CeO$_2$ or CeSiO$_4$ in these conditions (mass yield below 20% compared to quasi-quantitative precipitation at higher pH).

Furthermore, hydrothermal treatments performed in alkaline media (i.e. for pH ≥ 11) did not lead to the formation of CeSiO$_4$ due to the low dissolution rate of the Ce(III) silicate based precursors. This could be directly correlated to the low solubility of these precursors in alkaline conditions due to kinetics and/or thermodynamic factors. From this point of view, performing hydrothermal treatment with an initial pH close to pH = 7 appeared as the best compromise to prepare CeSiO$_4$.

An important decrease of the pH value during the hydrothermal treatment (from initial pH = 7 to final pH = 2) was observed in conditions that favored the formation of CeSiO$_4$ (Table S1). However, it remains unclear whether this pH evolution was linked to the oxidation of Ce(III) species or controlled by CeSiO$_4$ solubility equilibrium. Among the precursors used for these experiments, Ce$_{4.67}$(SiO$_2$)$_2$O and A-Ce$_2$Si$_2$O$_7$ were the best reactants to form pure CeSiO$_4$. Indeed, using Ce$_2$SiO$_5$ as starting reactant generally led to mixtures of CeO$_2$ and CeSiO$_4$ (Figure S3). This result was explained by the high sensibility of Ce$_2$SiO$_5$ to oxidation compared to the other Ce(III) silicates, which could induce a fast increase of Ce(IV) concentration in solution and then, the precipitation of Ce(IV) hydroxide.$^{19}$ Using G-Ce$_2$Si$_2$O$_7$ as starting reactant in the same conditions led to mixtures of G-Ce$_2$Si$_2$O$_7$ and CeSiO$_4$. This latter result could be explained by the refractory character of G-Ce$_2$Si$_2$O$_7$ associated to lower dissolution kinetics compared to others precursors. Furthermore, kinetic studies performed on Ce$_{4.67}$(SiO$_2$)$_2$O (Figure S5) and A-Ce$_2$Si$_2$O$_7$ (Figure 4) as starting precursors allowed to observe their complete conversion into CeSiO$_4$ after 3 days of hydrothermal treatment at 150°C in nitric media with an initial pH equal to 7.

In order to understand if the lower reactivity of G-Ce$_2$Si$_2$O$_7$ could be correlated to the temperature of the thermal treatment required to form this phase (9 hours, 1550°C, Ar – 4% H$_2$), syntheses of Ce$_{4.67}$(SiO$_2$)$_2$O were also performed in the same conditions. This heating treatment did not induce any significant change in the behavior of the Ce(III) silicate precursor compared to the heating treatment performed at 1350°C. Thus, the low reactivity of G-Ce$_2$Si$_2$O$_7$ could be linked to the nature of the phase rather than to its better crystallinity or lower reactive surface area compared to others precursors.

Experiments have been also performed in order to determine if the mechanical grinding step (performed before the Ce(III) solid silicate synthesis) alone was sufficient to explain the formation of CeSiO$_4$. To this aim, hydrothermal syntheses were made at 150°C from stoichiometric amounts of CeO$_2$ and SiO$_2$ mechanically milled together for 1 hour at 30 Hz and with different pH values. CeSiO$_4$ did not form during these experiments. Therefore, the use of Ce(III) silicate precursor seems to be necessary to prepare CeSiO$_4$. This result is in good agreement with the ab initio calculation which predicts that CeSiO$_4$ is less stable than the mixture of CeO$_2$ and SiO$_2$. Because experiments performed in air led to the formation of pure CeSiO$_4$, it appeared that the working atmosphere was not a key parameter controlling the formation of CeSiO$_4$, contrarily to what was observed with the aqueous Ce(III) species.$^{29,30}$

The impact of the temperature of the hydrothermal treatment on the yield of formation of CeSiO$_4$ was also studied through various experiments between 60°C and 250°C starting from Ce$_{4.67}$(SiO$_2$)$_2$O and A-Ce$_2$Si$_2$O$_7$ precursors (Figure 5 and Figure S6). CeSiO$_4$ was formed between 60°C and 150°C from both precursors. At T = 250°C, a large amount of crystallized CeO$_2$ was formed while only small amounts of CeSiO$_4$ were obtained. Such a temperature limit is in good agreement with the one obtained from aqueous Ce(III) precursors.$^{30}$

Moreover, thanks to SEM observations, a change in the morphology of the grains was observed during the hydrothermal treatment. Indeed, A-Ce$_2$Si$_2$O$_7$ adopted a
microstructure characteristic of sintered samples, whereas the final CeSiO$_4$ grains exhibited the square-based bipyramid morphology characteristic of zircon-type materials (Figure 6). The same changes were also observed during the conversion of Ce$_4$Si$_2$(SiO$_4$)$_3$O. Therefore, the formation of CeSiO$_4$ from Ce(III) silicate precursors surely required the progressive dissolution of the starting precursor, the oxidation of Ce(III) to Ce(IV) in solution and then, the precipitation of CeSiO$_4$.

**Preparation of CeSiO$_4$ in hydrochloric medium**

In order to underline the potential role of nitric acid during the synthesis of CeSiO$_4$, especially through the development of redox reactions with cerium, several experiments were made from Ce$_4$Si$_2$(SiO$_4$)$_3$O, A-Ce$_2$Si$_2$O$_7$ and G-Ce$_2$Si$_2$O$_7$ in hydrochloric media. It should be noted that both hydrochloric and nitric acids are strong acids in this concentration range and that the complexing power of nitrate and chloride anions may be inferred to be similar. In contrast, nitric acid is often an oxidizing agent while hydrochloric acid is usually considered as a more reducing medium. Hydrothermal treatments were carried out in air for 7 days at 150°C, with pH values ranging from pH = 2 to 7. All of these experiments led to the partial conversion of the starting precursors into CeSiO$_4$ (Figure 7-a and Figure 7-b).

As observed for G-Ce$_2$Si$_2$O$_7$, extending the duration of the hydrothermal treatment induced the increase of the yield of formation of CeSiO$_4$ (Figure 7-b). Therefore, it was concluded that the kinetics of formation of CeSiO$_4$ were lower in hydrochloric media than in nitric media (Figure 2 and Figure 7). This difference could be attributed to the presence of nitrous acid, issued from the reduction of HNO$_3$ during the oxidation of Ce(III), which speeds up the kinetics of formation of CeSiO$_4$.

SEM observations performed on G-Ce$_2$Si$_2$O$_7$ and CeSiO$_4$ confirmed the morphological change already noted in nitric medium. Indeed, from the features characteristic of a sintered sample obtained for G-Ce$_2$Si$_2$O$_7$, the morphology turned into a square-based bipyramid morphology for CeSiO$_4$ (Figure 8). Moreover, in these conditions, which allowed a slow oxidation process, an epitaxial growth of CeSiO$_4$ was observed leading to a prism-like morphology characteristic of the zircon-type silicates growth (the spherical particles observed in Figure 8-b may correspond to residual Ce$_2$Si$_2$O$_7$ or SiO$_2$).

**Characterization of CeSiO$_4$ samples**

To summarize, the multiparametric study developed to prepare pure CeSiO$_4$ allowed to determine optimal conditions, which correspond to the following guidelines:

**Figure 6.** SEM micrograph obtained for A-Ce$_2$Si$_2$O$_7$ (T = 1530°C for 9 hours, Ar – 4% H$_2$ (a) and for CeSiO$_4$ obtained after hydrothermal conditions (T = 150°C, t = 7 days) under air atmosphere from A-Ce$_2$Si$_2$O$_7$ in nitric medium and pH = 7.0 (10) (b).

**Figure 7.** PXRD patterns obtained after hydrothermal treatment (7 days and T = 15°C (a) or 21 days and T = 15°C (b)) under air atmosphere starting from G-Ce$_2$Si$_2$O$_7$ precursor, in hydrochloric media and with initial pH equal to 7.2 (19), 3.3 (20), 2.2 (21), 7.2 (22), 3.1 (23) or 2.1 (24). Characteristic XRD lines of CeO$_2$, CeSiO$_4$, and G-Ce$_2$Si$_2$O$_7$ were extracted from ref 32, 9 and 18, respectively.

**Figure 8.** SEM micrograph obtained for starting G-Ce$_2$Si$_2$O$_7$ precursor (9 hours, T = 1550°C, under Ar – 4% H$_2$ (a) and for CeSiO$_4$ obtained after hydrothermal treatment (T = 150°C and t = 21 days) under air atmosphere in hydrochloric medium and with pH = 7.0 (10) (b).
- A-Ce$_2$Si$_2$O$_7$ or Ce$_{6.67}$(SiO$_4$)$_3$O used as Ce(III) starting precursors due to their favorable behavior (in terms of kinetics) during dissolution tests;
- nitric medium, to be preferred over hydrochloric one;
- hydrothermal treatment in air with a starting pH value adjusted to 7.0, a temperature of 150°C and maintained for at least 3 days.

For such optimized conditions, the Rietveld refinement of XRD data led to the following unit cell parameters:

\[ a = 6.9523(2) \text{ Å} \]

\[ c = 6.2036(2) \text{ Å} \]

\[ V = 300.06(2) \text{ Å}^3 \] (Figure 9). These values is in good agreement with those obtained when using aqueous Ce(III) precursors

\[ a = 6.9603(1) \text{ Å} \]

\[ c = 6.1946(2) \text{ Å} \]

\[ V = 300.11(2) \text{ Å}^3 \] and with those reported by Skakle et al. (a = 6.9564(3) Å and c = 6.1953(4) Å, i.e. V = 299.80(3) Å³). Moreover, infrared and Raman spectra recorded on these samples were characteristic of the features obtained for CeSiO$_4$ (Table S3, Figure S8 and Figure S9).

In order to complete the characterization of pure CeSiO$_4$, XANES and EXAFS experiments were performed at the Ce L$_{III}$ edge. The sample studied was prepared after hydrothermal treatment in nitric medium (150°C, 7 hours, pH = 7) starting from A-Ce$_2$Si$_2$O$_7$. On the XANES spectra, the CeSiO$_4$ sample is characterized by a white line double peaks of roughly equal intensity with maxima at 5731 eV and 5738 eV (Figure 10). These double peaks are characteristic of tetravalent cerium corresponding to the $2p_{3/2} \rightarrow (4f_L)5d$, and $2p_{3/2} \rightarrow (4f^0)5d$ electron transitions (L denotes relaxation transition of an electron from oxygen 2p to cerium 4f orbital) and their locations in good agreement with literature references, while trivalent cerium would be characterized by a single peak at 5727 eV (originating from the electron transition $2p_{3/2} \rightarrow (4f^1)5d$) (Figure 10). Therefore, the XANES spectra tends to confirm the oxidation state +IV expected for CeSiO$_4$. It could also be noticed that the shoulder usually observed at 5728 eV on the CeO$_2$ spectra (used as Ce(IV) reference in Figure 10), was not observed for CeSiO$_4$ probably because of the differences of Ce-O bonds local geometry in these two phases.

In order to confirm the Ce environment in CeSiO$_4$, pseudo-radial distribution function was determined from the Fourier transform of the EXAFS spectrum ($k = 2–10$ Å$^{-1}$). The data analysis was based on the model structure reported in the literature for the crystal structure of CeSiO$_4$. Only Debye-Waller factors were adjusted variables whereas coordination numbers and distances were fixed to crystallographic values.

Figure 10. Ce L$_{III}$ edge XANES spectrum (a) and respective first derivative (b) of Ce(III) and Ce(IV) references 38 and CeSiO$_4$ prepared under hydrothermal conditions (T = 150°C, t = 7 days) in nitric medium and with pH = 7.0, starting from A-Ce$_2$Si$_2$O$_7$ precursor (10).
The spectra obtained from these simulations were found to be in good agreement with the experimental data (Figure 11 and Table 2). The first peak was assigned to the oxygen atoms present in the first coordination sphere of cerium whereas the two following peaks were attributed to the silicon atoms present in the second coordination sphere, which correspond to bidentate and monodentate silicate bonds, respectively. At longer distance, a third contribution was associated to the Ce-Ce interactions. All of these results confirmed the formation of a zircon-type CeSiO₃ (I₄₁/amd space group), resulting from the oxidation of Ce(III) into Ce(IV) under hydrothermal conditions.

Discussion regarding the formation mechanism of CeSiO₄

According to the SEM observations, it may be inferred that the formation of CeSiO₄ relies on the low dissolution rates of the Ce(III) silicate starting precursor. This mechanism correspond to the oxidative dissolution of Ce(III) silicate starting precursors, leading to the formation of Ce(IV)-silicate aqueous species which then precipitate as CeSiO₄. However, due to the suspected very low solubility of Ce(IV) silicate species, the precipitation of CeSiO₄ in the near field of the precursor and then the formation of a passivating layer on its surface may be expected with this mechanism. However, since no passivating layer was observed, a chemical path through aqueous Ce(III) silicate intermediate species seems to be more likely.

The precursors dissolution could also correspond to the hydrolysis of the Si-O-Si bonds, which could exist for all Ce(III) silicate species, and then could lead to the release of Ce(III) silicate based complexes in the reactive media. These complexes are subsequently oxidized to form Ce(IV) silicate species which play a key role during the precipitation of CeSiO₄ as already described for thorium and uranium (IV) silicates. The formation of Ce(IV) species may be enhanced by oxidizing species such as nitrogen based species coming from the decomposition of nitric acid and O₂ from air. According to this hypothesis, the corresponding formation mechanism may be explained by the following reactions:

\[
\text{[Ce(III)-silicate precursor]}^{\text{solid}} \rightleftharpoons \text{[Ce(III)-silicate complex]}^{\text{aq}}
\]

\[
\text{[Ce(III)-silicate complex]}^{\text{aq}} \rightleftharpoons \text{[Ce(IV)-silicate complex]}^{\text{aq}} + e^-
\]

\[
\text{[Ce(IV)-silicate complex]}^{\text{aq}} \rightleftharpoons \text{[Ce(IV)-silicate]}^{\text{solid}}
\]

Since no aqueous characterization allowed us to identify the intermediate species, their nature remains unknown. Indeed, Ce(III) silicate complexes chemistry is poorly documented. However, based on the data reported for M(III) silicate aqueous chemistry, the formation of Ce²⁺(OSi(OH))₃n complex in solution could be suspected. Moreover, the complexation by the nitrate anions must also be considered.

The aqueous Ce(III) species oxidation in nitric reactive media is most probably correlated to the reduction of nitrate ions through the following reactions:

\[
\text{HNO}_3 + \text{H}^+ + e^- \rightleftharpoons \frac{1}{2} \text{N}_2\text{O}_4 + \text{H}_2\text{O} \quad E^* = 0.803 \text{ V/ENH}
\]

\[
\text{HNO}_3 + 2 \text{H}^+ + 2 e^- \rightleftharpoons \text{HNO}_2 + \text{H}_2\text{O} \quad E^* = 0.934 \text{ V/ENH}
\]

\[
\text{HNO}_3 + 3 \text{H}^+ + 3 e^- \rightleftharpoons \text{NO}_2 + 2 \text{H}_2\text{O} \quad E^* = 0.957 \text{ V/ENH}
\]

The oxygen dissolved in the reactive media may also be involved in the oxidation of Ce(III). It may, more precisely, explain the formation of CeSiO₄ in hydrochloric reactive media.

\[
\frac{1}{2} \text{O}_2 + 2 \text{H}^+ + 2 e^- \rightleftharpoons \text{H}_2\text{O} \quad E^* = 1.229 \text{ V/ENH}
\]

As mentioned for the speciation of Ce(IV), there is only little data in the literature concerning nitrate and hydroxo ions and only extrapolated ones for silicate complexes. However, it is known that for actinides and lanthanides, the complexation for M(IV) is much more important than for M(III). This higher complexation obtained for M(IV)
Ce$^{4+} + e^- \rightarrow Ce^{3+}$

$E^\circ = 1.72 \text{ V/ENH}$

Indeed, as observed during the precipitation of CeO$_2$ at pH > 4 from Ce(III) reactants under aerated conditions, the precipitation of CeSiO$_4$ may be explained by the complexation of Ce(IV) in solution and a very low solubility of Ce(IV)-silicate aqueous species. It is noteworthy to mention that the Ce(IV)/Ce(III) standard potential may also be modified under hydrothermal conditions.

As reported in our previous study, CeSiO$_2$ was stable during hydrothermal treatment at 250°C. Therefore, the temperature limit observed for the conversion of Ce(III) silicate into CeSiO$_4$ was probably due to the destabilization of aqueous Ce(III) (and/or Ce(IV)) silicate intermediates for T > 150°C, and also of aqueous Ce(IV) silicate species with respect to hydroxide ones. In this context, the small amounts of CeSiO$_4$ observed for T > 150°C were surely formed during the beginning of the hydrothermal treatment (i.e., during the rise of temperature).

From a more general point of view, the formation of CeSiO$_4$ from Ce(III) silicate solid precursors appeared to be more efficient and easier than working directly from aqueous Ce(III) precursors. Indeed, this original way of preparation enabled to work on a wider pH range with a good recovery yield and without any constraint coming from the working atmosphere. This difference may result from the slow dissolution and oxidation (or oxidative dissolution) of Ce(III) starting precursors, leading to low concentrations in the reactive media which disfavored the cerium (IV) and cerium (III) hydrolysis.

**Conclusions**

CeSiO$_4$ was successfully formed from several solid Ce(III) based precursors, i.e. Ce$_2$SiO$_4$, Ce$_{67}$(SiO$_4$)$_3$O, A-Ce$_2$Si$_2$O$_7$ and G-Ce$_5$Si$_3$O$_7$ after hydrothermal treatment under air atmosphere. For several of them, their slow conversion allowed the preparation of single phase CeSiO$_4$ with higher recovery yields compared to those obtained when starting from mixtures of cerium and silicate solutions. The optimized conditions to form pure CeSiO$_4$ were based on hydrothermal treatment for 7 days at T ≤ 150°C (nitric medium) starting from A-Ce$_2$Si$_2$O$_7$ or Ce$_{67}$(SiO$_4$)$_3$O precursor. Since CeSiO$_4$ was not obtained from Ce(IV) precursors due to the formation of CeO$_2$, as a consequence of the rapid hydrolysis of Ce(IV), the redox state of cerium in the starting precursor appeared as a key parameter. The formation of CeSiO$_4$ was directly correlated to the formation of Ce(III) silicate aqueous species which were slowly oxidized in situ during the hydrothermal treatment to form Ce(IV) silicate.

In addition, the reactivity of such Ce(III)-based silicates in representative conditions of environmental situations (pH = 7 and 60°C ≤ T ≤ 150°C) raises important questions about their evolution in conditions characteristic for several of their reported applications (including wet environments).

It can also pave the way to a better understanding of the potential reactivity of actinide(III) silicate phases such as the solid Pu(III) silicate phases obtained by Fortner et al. by vapor phase hydration of borosilicate glasses and, therefore, of the behavior of plutonium in nuclear waste repository conditions.

**Conflicts of interest**

There are no conflicts to declare.

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**Notes and references**


